

PROCESS FOR TREATING ONO DIELECTRIC FILM  
OF A FLOATING GATE MEMORY CELL

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5 ABSTRACT

A process to deposit a silicon dioxide layer on a silicon nitride layer for an ONO stack of a floating gate transistor. Silicon dioxide is deposited on a silicon nitride layer and annealed in a batch furnace or a single wafer rapid thermal anneal tool in a nitrogen oxide (NO) or nitrous oxide (N<sub>2</sub>O) ambient environment.

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